

Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)	<i>Complete if Known</i>	
	<b>Application Number</b>	10/612,793
	<b>Filing Date</b>	July 2, 2003
	<b>First Named Inventor</b>	Arup Bhattacharyya
	<b>Group Art Unit</b>	2826
	<b>Examiner Name</b>	Thomas Dickey
Sheet 1 of 1	Attorney Docket No: 1303.111US1	

US PATENT DOCUMENTS				
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate
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/TD/	US-6,845,034	01/18/2005	Bhattacharyya, A.	03/11/2003
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OTHER DOCUMENTS – NON PATENT LITERATURE DOCUMENTS		
Examiner Initials*	Include name of the author (In CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>1</sup>
/TD/	LEE, S. W, et al., "Low Temperature Poly-Si Thin Film Transistor Fabrication by Metal-Induced Lateral Crystallization", IEEE Electron Device Letters, (April 1996), 160-162	

EXAMINER

/Thomas Dickey/

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